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(54)	POSITIVE RESIST COMPOSITION AND PATTERN FORMING METHOD USING THE SAME				
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See application file for complete search history.

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ABSTRACT

A positive resist composition satisfying high sensitivity, high resolution and good line edge roughness at the same time, and a pattern forming method using the composition, are provided, which is a positive resist composition comprising (A) a resin of which solubility in an alkali developer increases under the action of an acid, the resin containing a repeating unit having a specific styrene skeleton and a repeating unit having a specific ring structure, and (B) a compound of generating an acid upon irradiation with actinic rays or radiation; and a pattern forming method using the composition.

20 Claims, No Drawings

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